

B. Specification

Please amend the paragraph at page 28, line 22, to page 29, line 4, as follows:

--The comparative sample C was observed with the FE-SEM (field emission scanning electron microscope). In the sample surface viewed from right above the substrate, the boundary between aluminum and silicon could not be observed clearly. That is, the aluminum nanostructured material could not be verified. In other words, under the substrate temperature being too high, the state becomes ~~stablier~~ more stable, so that it is assumed that the film growth for forming the aluminum nanostructured material cannot be attained.--

Please amend the paragraph at page 67, line 18, to page 68, line 14, as follows:

--Platinum columnar structured materials were produced through the electrodeposition (electroplating) from the bottom of this porous oxidized silicon film. The porous oxidized silicon thin film produced in the above steps was put in a commercially available electroplating solution (electroplating solution for platinum produced by Kojundo Chemical Laboratory Co., Ltd.; product code: PT-100E), and the electrodeposition was performed at a current density of 1.5 A/dm² in an acid bath kept at 70°C (pH = 0.1) for 120 seconds in an acid bath kept at 70°C (pH = 0.1), thereby depositing platinum on the oxidized silicon film as well as in the holes. The substrate after the electrodeposition was thoroughly rinsed with pure water and then dried. At this time, it was found that platinum ~~overflow~~ overflowed from the holes by performing the electrodeposition for a long period of time, which resulted in a thin film on the oxidized silicon film. This is conceivable to be that because a distance between one hole and

another hole is close, and thus after electrodeposited platinum overflows from the holes, its growth progresses in a lateral direction as well, so that the entire surface is covered therewith.--